N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Please click here to visit our online spice models database.

Features

- Low On-Resistance: $R_{DS(ON)}$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected Up To 2kV**
- **"Green" Device (Note 4)**

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.002 grams (approximate)

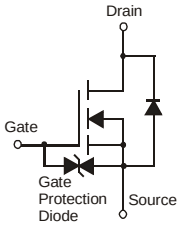
SOT-523



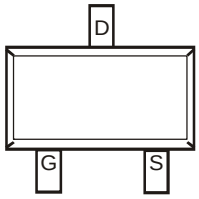
ESD Protected up to 2kV



TOP VIEW



EQUIVALENT CIRCUIT



TOP VIEW

Pin Out Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current (Note 1)	Continuous Pulsed (Note 3)	I_D	300 800	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_D	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.6	2.5	V	V_{DS} = 10V, I_D = 1mA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	— —	2.0 3.0	Ω	V_{GS} = 10V, I_D = 0.5A V_{GS} = 5V, I_D = 0.05A
Forward Transfer Admittance	$\|Y_{fs}\|$	80	—	—	ms	V_{DS} =10V, I_D = 0.2A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5.0	pF	

Notes:
1. Device mounted on FR-4 PCB.
2. No purposefully added lead.
3. Pulse width ≤10μS, Duty Cycle ≤1%
4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
5. Short duration pulse test used to minimize self-heating effect.

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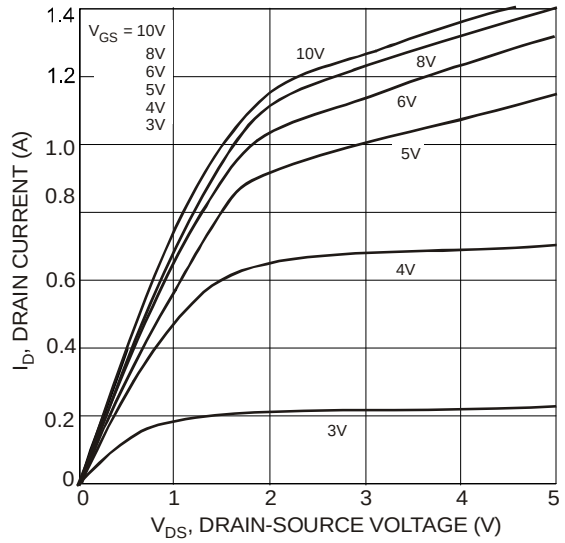


Fig. 1 Typical Output Characteristics

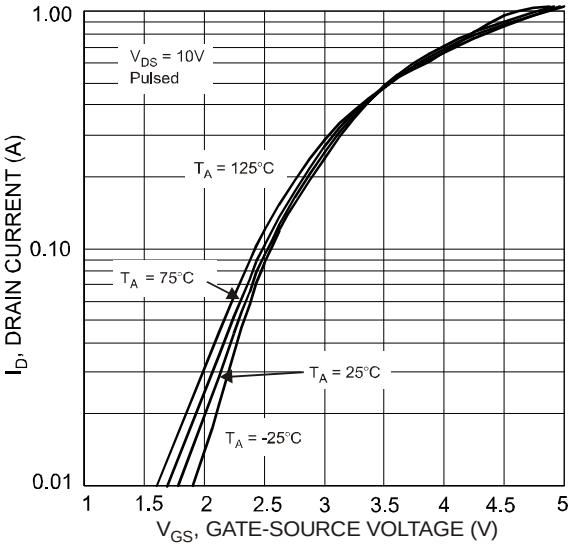


Fig. 2 Typical Transfer Characteristics

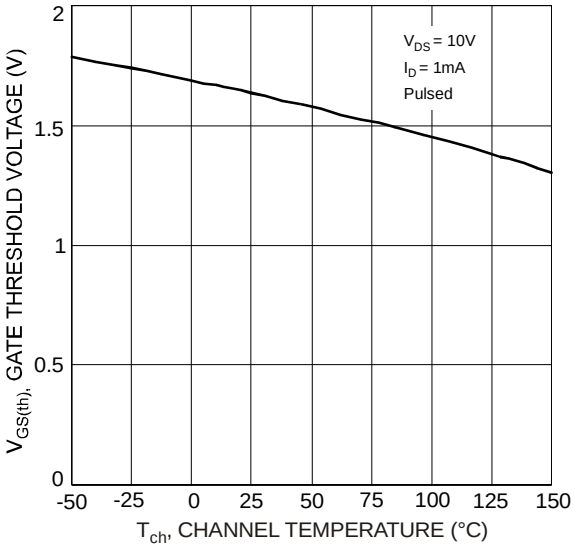


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

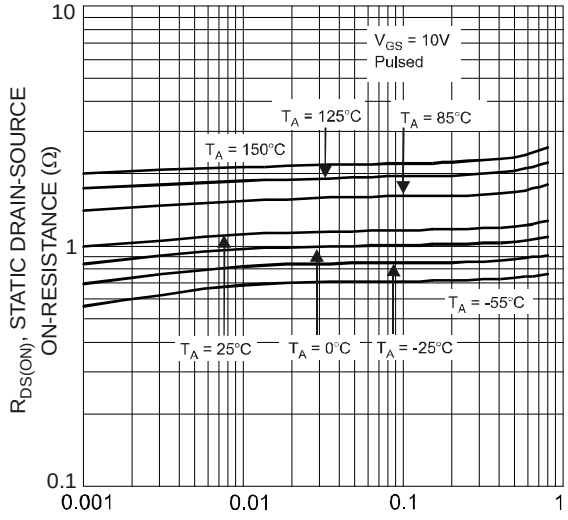


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

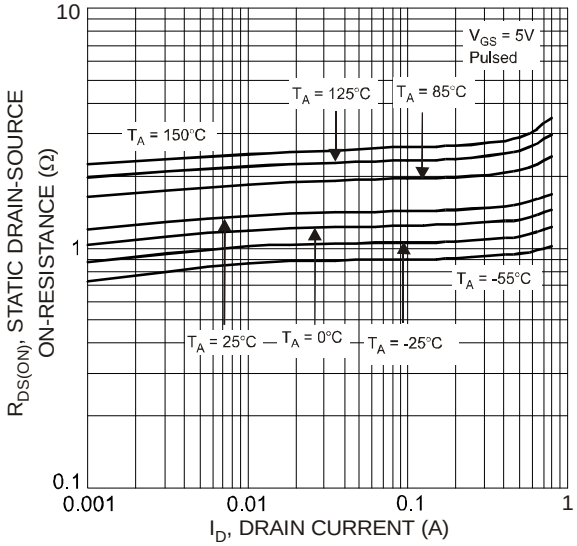


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

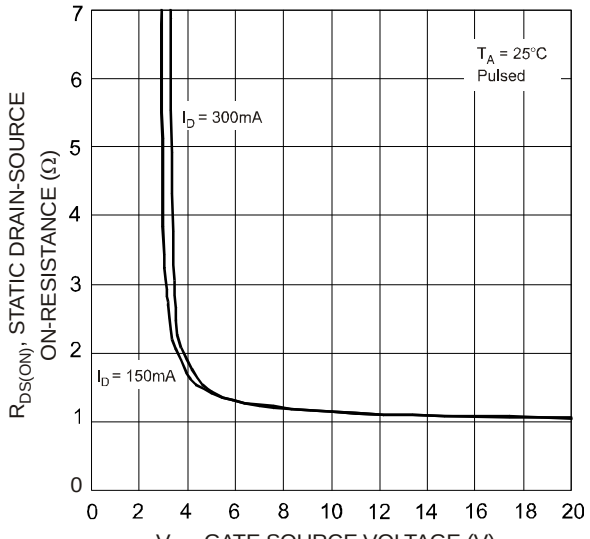


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

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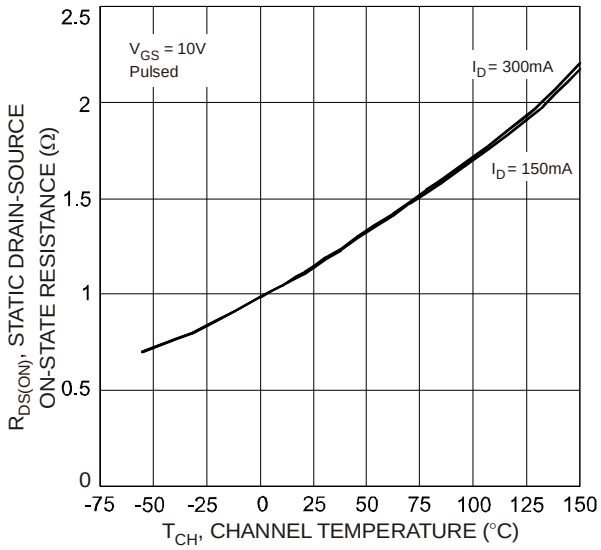


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

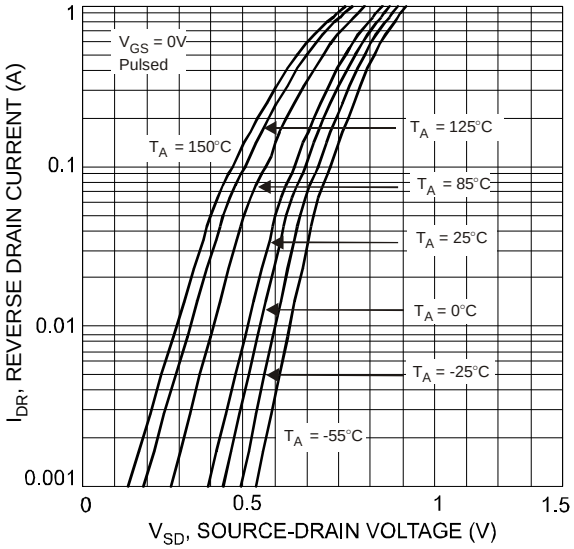


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

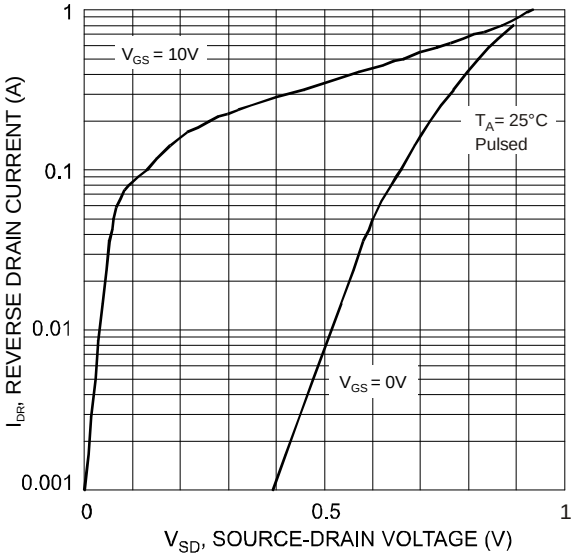


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

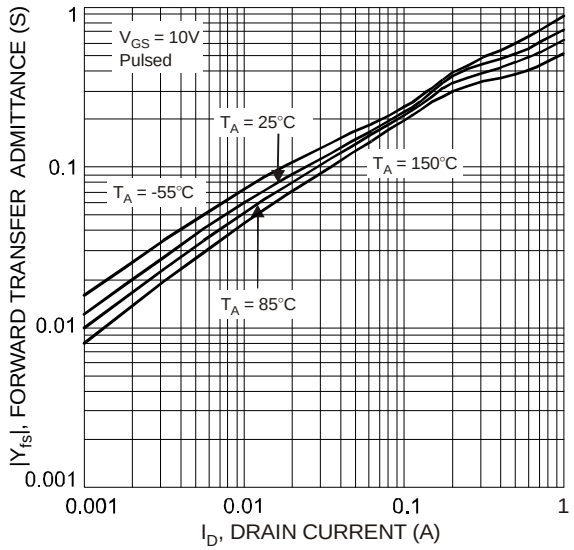


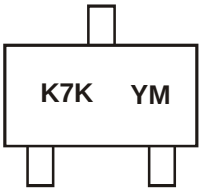
Fig.10 Forward Transfer Admittance vs. Drain Current

Ordering Information (Note 6)

Part Number	Case	Packaging
DMN601TK-7	SOT-523	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K7K = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: S = 2005)
M = Month (ex: 9 = September)

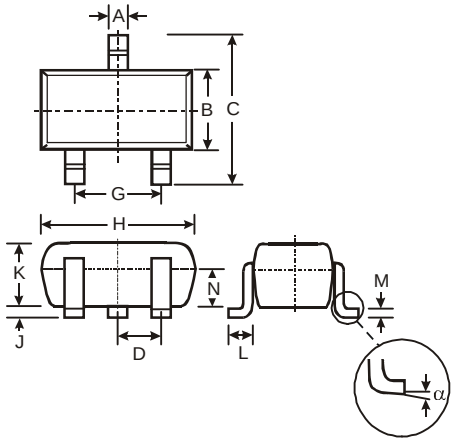
Date Code Key

Year	2005	2006	2007	2008	2009	2010	2011	2012
Code	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

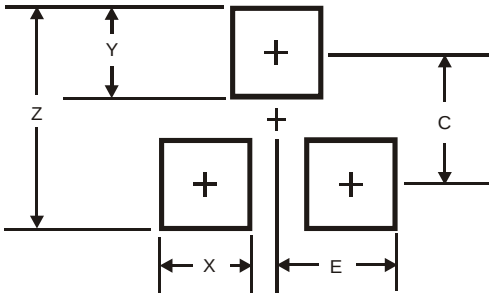
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Package Outline Dimensions



SOT-523			
Dim	**Min**	**Max**	**Typ**
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.8
X	0.4
Y	0.51
C	1.3
E	0.7

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